

SKiiP 26AC065V1



MiniSKiiP® 2

3-phase bridge Inverter

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Features

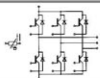
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connection
- UL recognised file no. E63532

Typical Applications

- Inverter up to 12,5 kVA
- Typical motor power 5,5 kW

Remarks

- V_{CEsat} , V_F = chip level value



AC

Absolute Maximum Ratings		$T_B = 25\text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter			
V_{CES}		600	V
I_C	$T_B = 25\text{ (70) }^\circ\text{C}$	56 (42)	A
I_{CRM}	$t_p \leq 1\text{ ms}$	100	A
V_{GES}		± 20	V
T_J		-40 ... +150	$^\circ\text{C}$
Diode - Inverter			
I_F	$T_B = 25\text{ (70) }^\circ\text{C}$	40 (30)	A
I_{FRM}	$t_p \leq 1\text{ ms}$	100	A
T_J		-40 ... +150	$^\circ\text{C}$
I_{RMS}	per power terminal (20 A / spring)	100	A
T_{stg}	$T_{op} \leq T_{stg}$	-40 ... +125	$^\circ\text{C}$
V_{scd}	AC, 1 min.	2500	V

Characteristics		$T_B = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 50\text{ A}$, $T_J = 25\text{ (125) }^\circ\text{C}$		2 (2,2)	2,5 (2,7)	V
$V_{GE(0)}$	$V_{CE} = V_{CE}$, $I_C = 1\text{ mA}$	3	4	5	V
$V_{CE(TD)}$	$T_J = 25\text{ (125) }^\circ\text{C}$		1,2 (1,1)	1,3 (1,2)	V
r_{T}	$T_J = 25\text{ (125) }^\circ\text{C}$		16 (22)	24 (30)	m Ω
C_{ios}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2,7		nF
C_{oos}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,8		nF
C_{rss}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,6		nF
$R_{th(j-s)}$	per IGBT		0,75		K/W
$t_{(on)}$	under following conditions		35		ns
t_r	$V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$		35		ns
$t_{(off)}$	$I_{Cnom} = 50\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		240		ns
t_f	$R_{Coff} = R_{Coff} = 15\text{ }\Omega$		25		ns
E_{on}	inductive load		1,3		mJ
E_{off}			0,9		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{FRom} = 50\text{ A}$, $T_J = 25\text{ (125) }^\circ\text{C}$		1,9 (1,9)	2,3 (2,4)	V
$V_{(TD)}$	$T_J = 25\text{ (125) }^\circ\text{C}$		1 (0,9)	1,1 (1)	V
r_{T}	$T_J = 25\text{ (125) }^\circ\text{C}$		18 (20)	24 (28)	m Ω
$R_{th(j-s)}$	per diode		1,5		K/W
I_{FRM}	under following conditions		42		A
O_{rr}	$I_{FRom} = 50\text{ A}$, $V_R = 300\text{ V}$		3,6		μC
E_{rr}	$V_{CE} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		0,8		mJ
	$di_p/dt = 1500\text{ A}/\mu\text{s}$				
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) }^\circ\text{C}$		1000(1670)		Ω
Mechanical Data					
m			65		g
M_b	Mounting torque	2		2,5	Nm

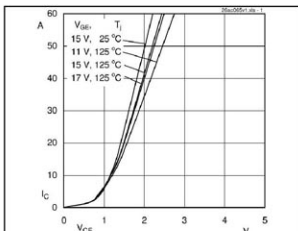


Fig. 1 Output characteristic

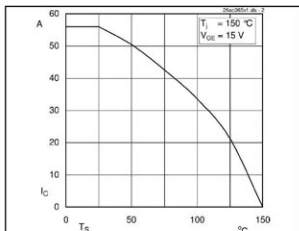


Fig. 2 Rated current vs. temperature

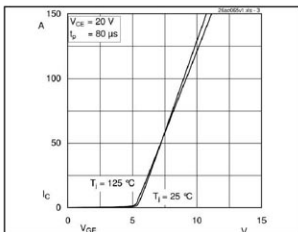


Fig. 3 Typ. transfer characteristic

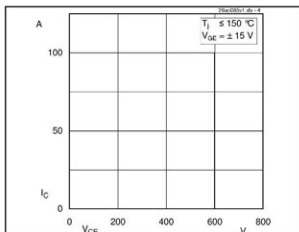


Fig. 4 Reverse bias safe operating area

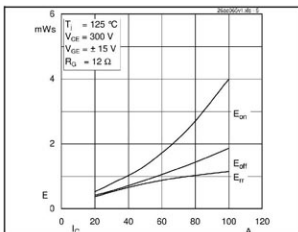


Fig. 5 Typ. Turn-on / off energy = $f(I_c)$

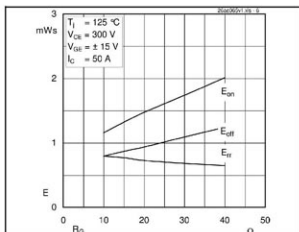
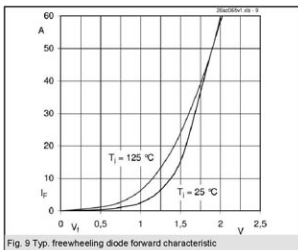
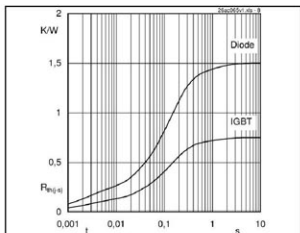
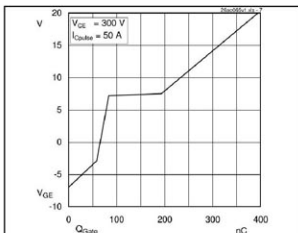
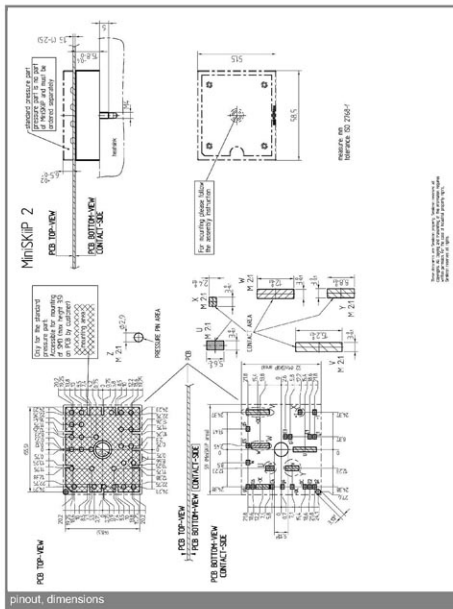
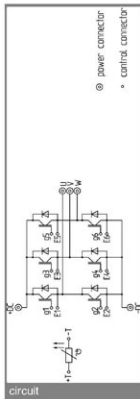


Fig. 6 Typ. Turn-on / off energy = $f(R_G)$





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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